

Silicon PIN Photodiode



DESCRIPTION

TEM7100X01 is a high speed and high sensitive PIN photodiode. It is a miniature surface mount device (SMD) including the chip with a 0.23 mm² sensitive area and a daylight blocking filter matched with IR emitters operating at wavelength of 830 nm to 950 nm.

FEATURES

- Package type: surface mount
- Package form: 0805
- Dimensions (L x W x H in mm): 2 x 1.25 x 0.85
- Radiant sensitive area (in mm²): 0.23
- High radiant sensitivity
- Daylight blocking filter matched with 830 nm to 950 nm emitters
- Fast response times
- Angle of half sensitivity: $\phi = \pm 60^\circ$
- Floor life: 168 h, MSL 3, acc. J-STD-020
- Lead (Pb)-free reflow soldering
- AEC-Q101 qualified
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition

AUTOMOTIVE
GRADERoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- High speed photo detector
- Infrared remote control
- Infrared data transmission
- Photo interrupters
- Shaft encoders

PRODUCT SUMMARY

COMPONENT	I_{ra} (μA)	ϕ (deg)	$\lambda_{0.5}$ (nm)
TEM7100X01	3	± 60	750 to 1050

Note

- Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TEM7100X01	Tape and reel	MOQ: 3000 pcs, 3000 pcs/reel	0805

Note

- MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	60	V
Power dissipation	$T_{amb} \leq 25^\circ\text{C}$	P_V	215	mW
Junction temperature		T_j	100	$^\circ\text{C}$
Operating temperature range		T_{amb}	- 40 to + 100	$^\circ\text{C}$
Storage temperature range		T_{stg}	- 40 to + 100	$^\circ\text{C}$
Soldering temperature	Acc. reflow solder profile fig. 8	T_{sd}	260	$^\circ\text{C}$
Thermal resistance junction/ambient	Acc. J-STD-051	R_{thJA}	270	K/W

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 50\text{ mA}$	V_F		1		V
Breakdown voltage	$I_R = 100\text{ }\mu\text{A}$, $E = 0$	$V_{(BR)}$	60			V
Reverse dark current	$V_R = 10\text{ V}$, $E = 0$	I_{ro}		1	3	nA
Diode capacitance	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$	C_D		4		pF
	$V_R = 5\text{ V}$, $f = 1\text{ MHz}$, $E = 0$	C_D		1.3		pF
Open circuit voltage	$E_e = 1\text{ mW/cm}^2$, $\lambda = 950\text{ nm}$	V_o		350		mV
Temperature coefficient of V_o	$E_e = 1\text{ mW/cm}^2$, $\lambda = 950\text{ nm}$	TK_{V_o}		- 2.6		mV/K
Short circuit current	$E_e = 1\text{ mW/cm}^2$, $\lambda = 950\text{ nm}$	I_k		3		μA
Temperature coefficient of I_k	$E_e = 1\text{ mW/cm}^2$, $\lambda = 950\text{ nm}$	TK_{I_k}		0.1		%/K
Reverse light current	$E_e = 1\text{ mW/cm}^2$, $\lambda = 950\text{ nm}$, $V_R = 5\text{ V}$	I_{ra}	2.4	3	3.6	μA
Angle of half sensitivity		ϕ		± 60		deg
Wavelength of peak sensitivity		λ_p		950		nm
Range of spectral bandwidth		$\lambda_{0.5}$		750 to 1050		nm
Rise time	$V_R = 10\text{ V}$, $R_L = 1\text{ k}\Omega$, $\lambda = 820\text{ nm}$	t_r		100		ns
Fall time	$V_R = 10\text{ V}$, $R_L = 1\text{ k}\Omega$, $\lambda = 820\text{ nm}$	t_f		100		ns

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

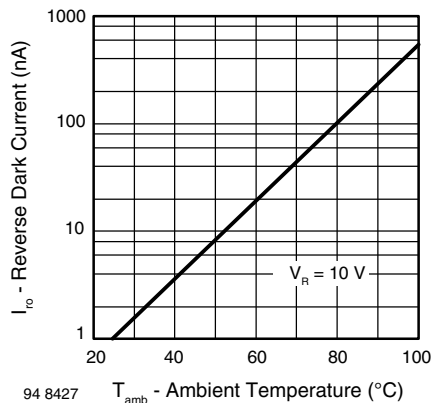


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

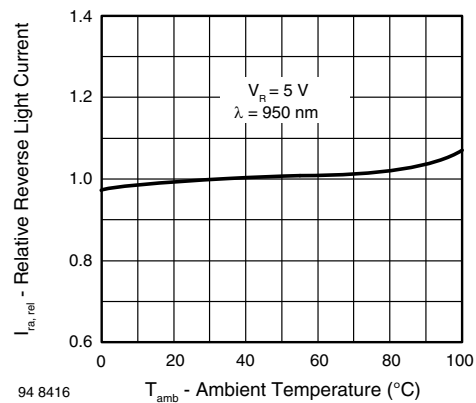
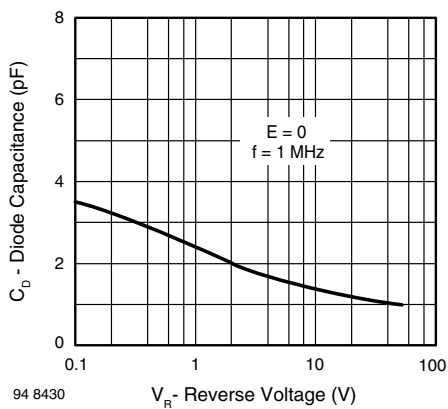
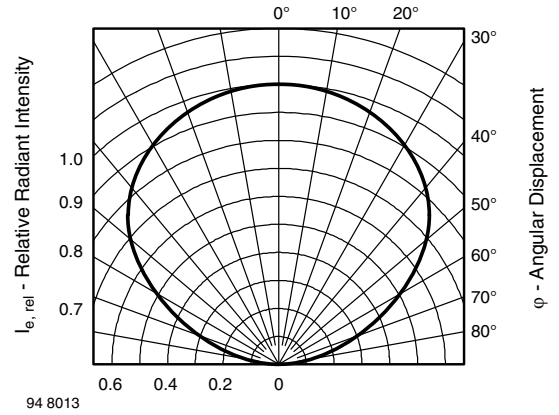
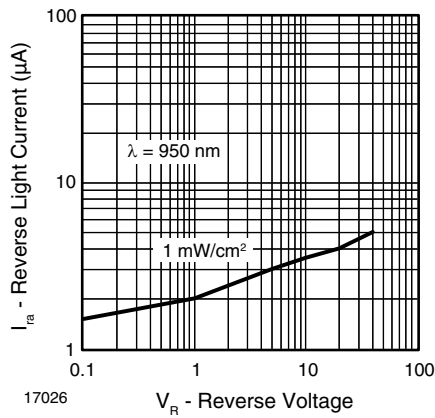
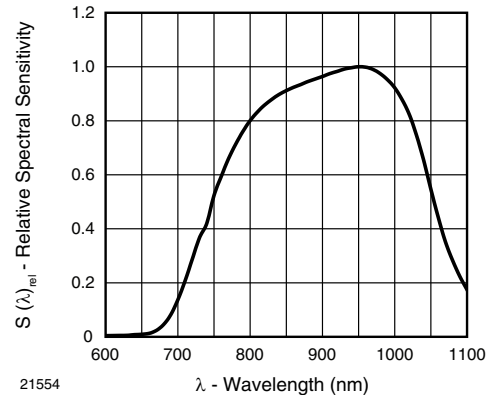
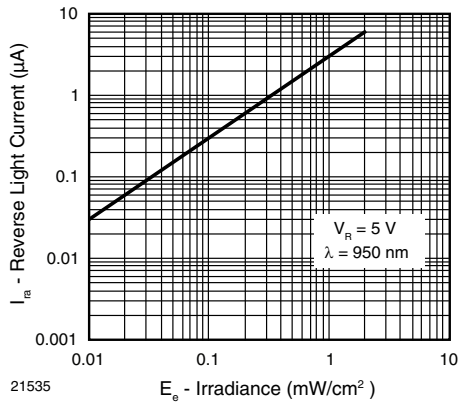


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature



REFLOW SOLDER PROFILE

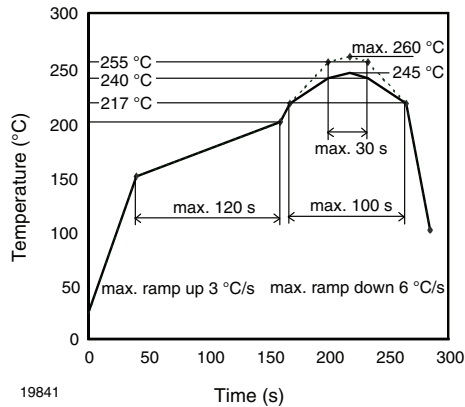


Fig. 8 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020

DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

FLOOR LIFE

Floor life (time between soldering and removing from MBB) must not exceed the time indicated on MBB label:

Floor life: 168 h

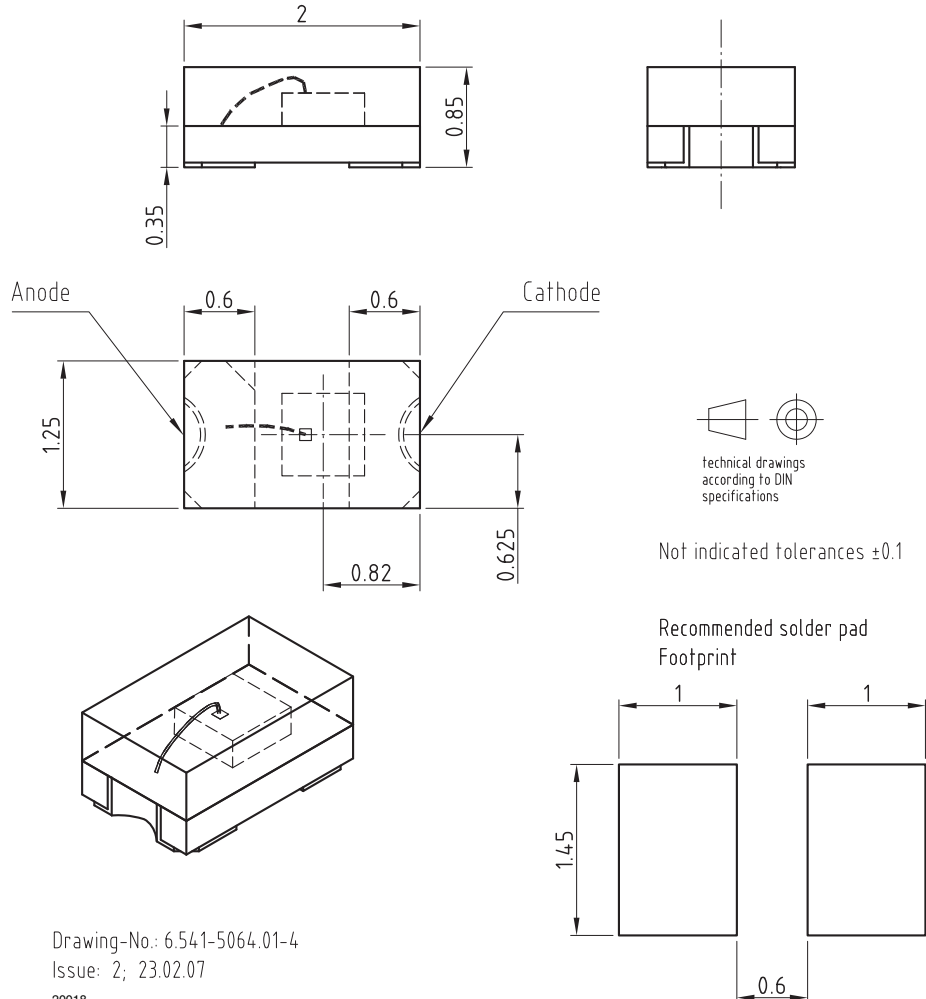
Conditions: $T_{amb} < 30\text{ °C}$, RH < 60 %

Moisture sensitivity level 3, acc. to J-STD-020.

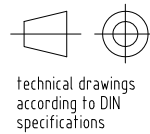
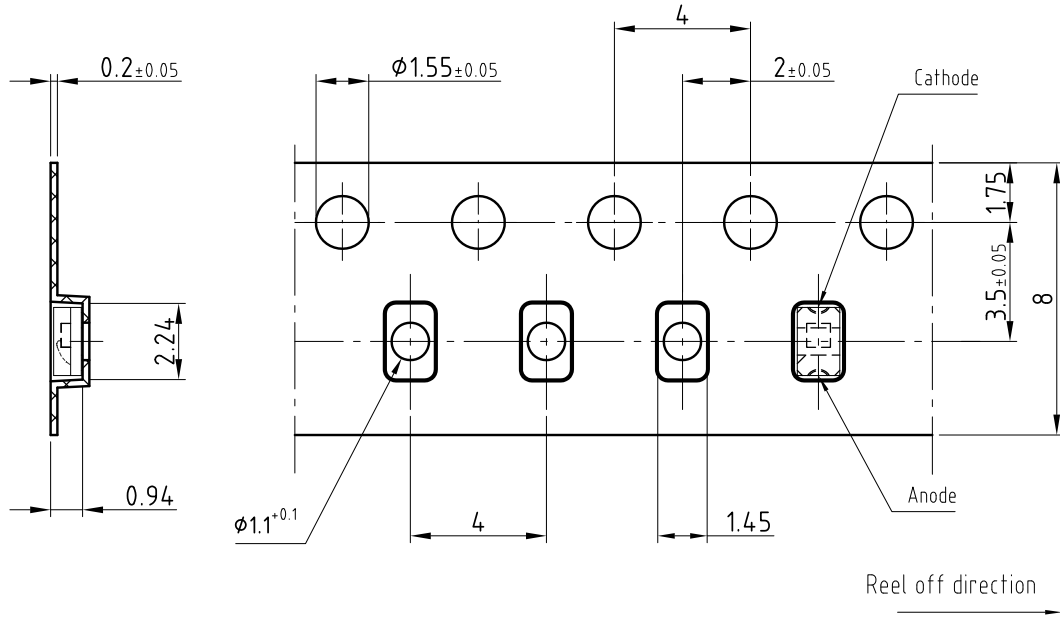
DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or label. Devices taped on reel dry using recommended conditions 192 h at 40 °C (+ 5 °C), RH < 5 %.

PACKAGE DIMENSIONS in millimeters



BLISTER TAPE DIMENSIONS in millimeters



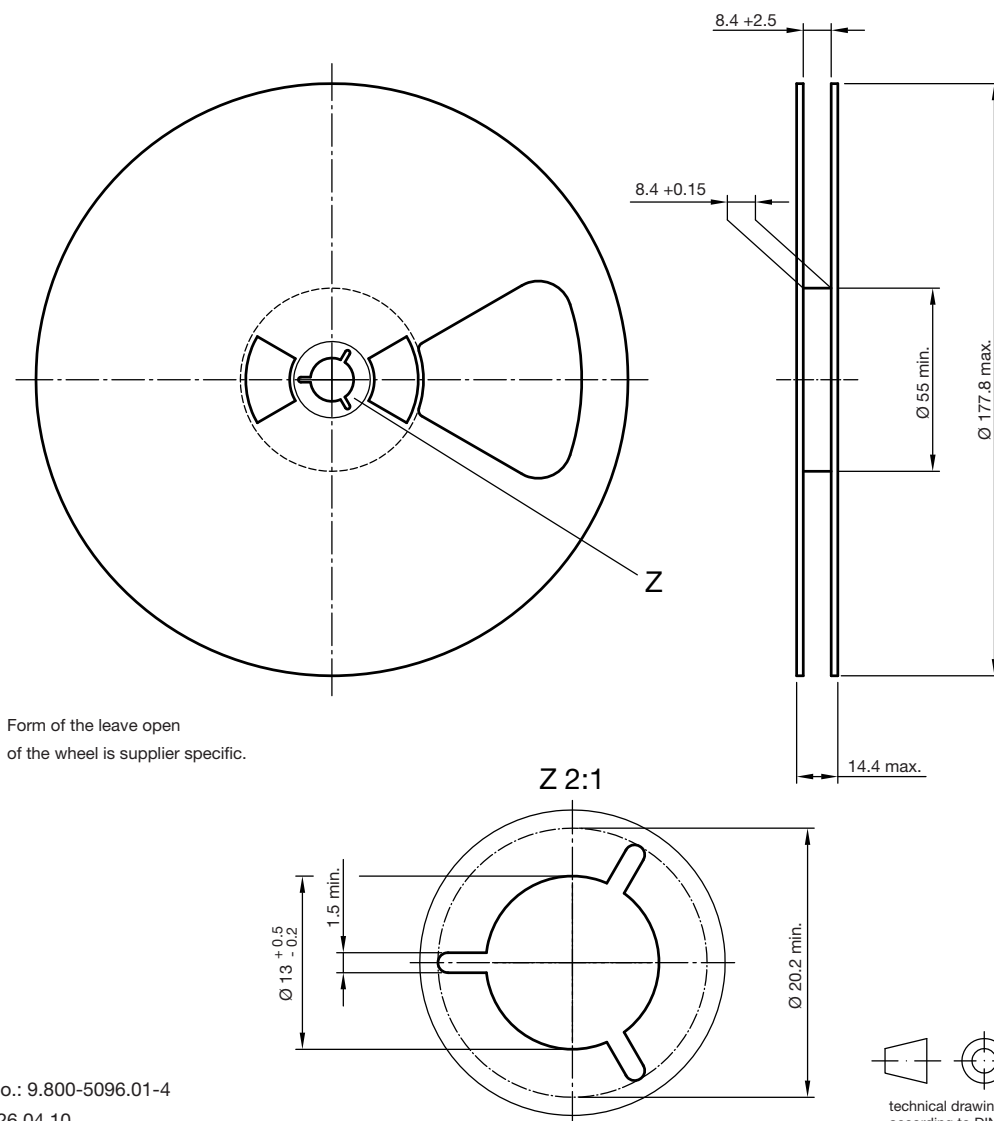
Drawing-No.: 9.700-5311.01-4

Issue: 1; 23.02.07

21501

Not indicated tolerances ± 0.1

REEL DIMENSIONS in millimeters



Drawing-No.: 9.800-5096.01-4

Issue: 2; 26.04.10

20875

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All product specifications and data are subject to change without notice.

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